



SMBF Plastic-Encapsulate Diodes

RS4ABF THRU RS4MBF Fast Recovery Rectifier Diodes

Features

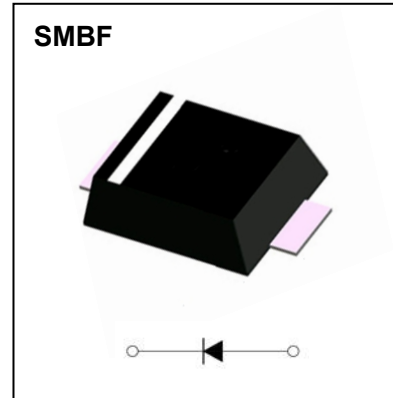
- $I_{F(AV)}$ 4A
- V_{RRM} 50V-1000V
- High surge current capability
- Polarity: Color band denotes cathode

Applications

- Rectifier

Marking

- RS4XBF
X : From A To M



Limiting Values(Absolute Maximum Rating)

Item	Symbol	Unit	Test Conditions	RS4						
				ABF	BBF	DBF	GBF	JBF	KBF	MBF
Repetitive Peak Reverse Voltage	V_{RRM}	V		50	100	200	400	600	800	1000
Maximum RMS Voltage	V_{RMS}	V		35	70	140	280	420	560	700
Average Forward Current	$I_{F(AV)}$	A	60Hz Half-sine wave, Resistance load, $T_L=100^\circ\text{C}$	4.0						
Surge(Non-repetitive)Forward Current	I_{FSM}	A	60Hz Half-sine wave, 1 cycle, $T_a=25^\circ\text{C}$	120						
Junction Temperature	T_J	$^\circ\text{C}$		-55 ~ +150						
Storage Temperature	T_{STG}	$^\circ\text{C}$		-55 ~ +150						

Electrical Characteristics (T=25°C Unless otherwise specified)

Item	Symbol	Unit	Test Condition	RS4						
				ABF	BBF	DBF	GBF	JBF	KBF	MBF
Peak Forward Voltage	V_F	V	$I_F=4.0\text{A}$	1.3						
Peak Reverse Current	I_{RRM1}	μA	$V_{RM}=V_{RRM}$	$T_a=25^\circ\text{C}$						
	I_{RRM2}			$T_a=125^\circ\text{C}$						
Thermal Resistance(Typical)	$R_{\theta J-A}$	$^\circ\text{C}/\text{W}$	Between junction and ambient	78						
Typical junction capacitance per diode	C_J	pF	Measured at 1.0MHz and applied reverse voltage of 4.0 volts.	68						
Maximum reverse recovery time	t_{rr}	ns	$I_F=0.5\text{A}, I_R=1.0\text{A}, I_{tr}=0.25\text{A}$	150		250		500		

Typical Characteristics

FIG.1: FORWARD CURRENT DERATING CURVE

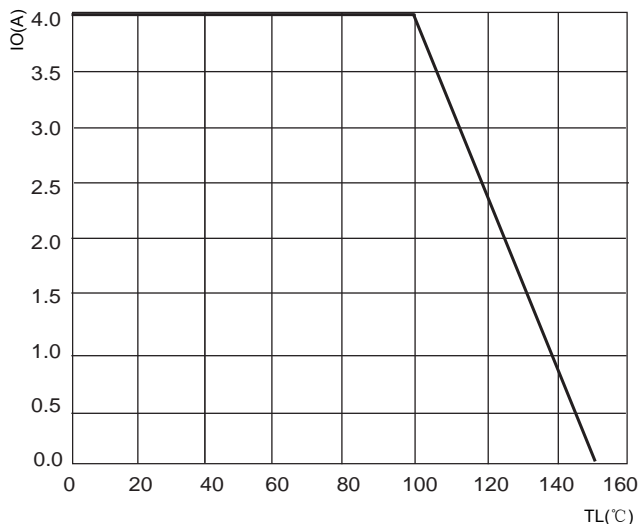


FIG.2: Surge Forward Current Capability

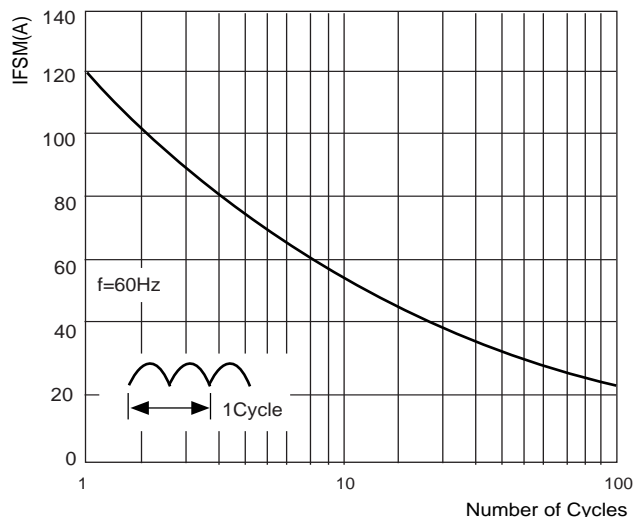


FIG.3: TYPICAL FORWARD CHARACTERISTICS

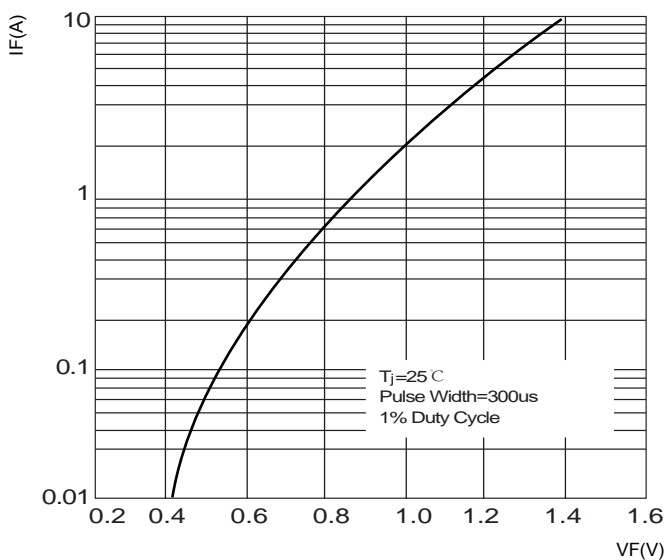


FIG.4 : TYPICAL REVERSE CHARACTERISTICS

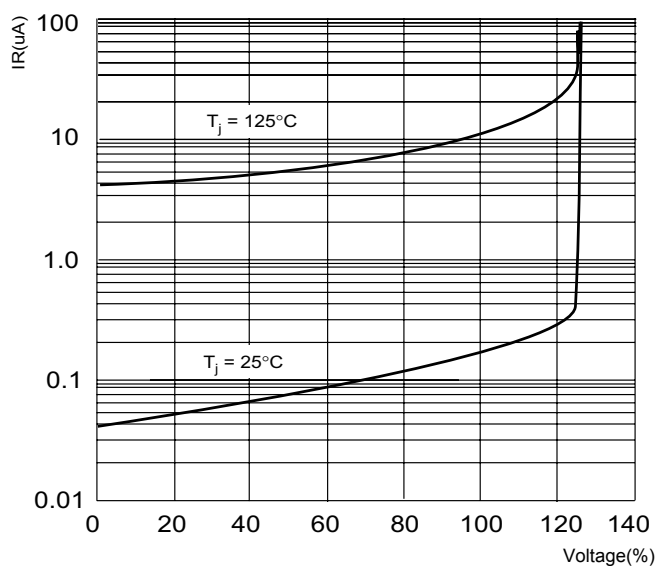
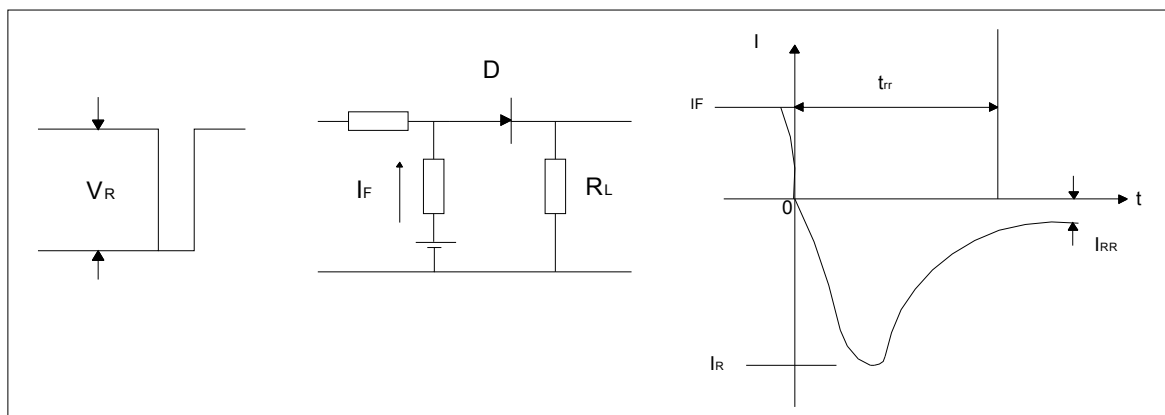
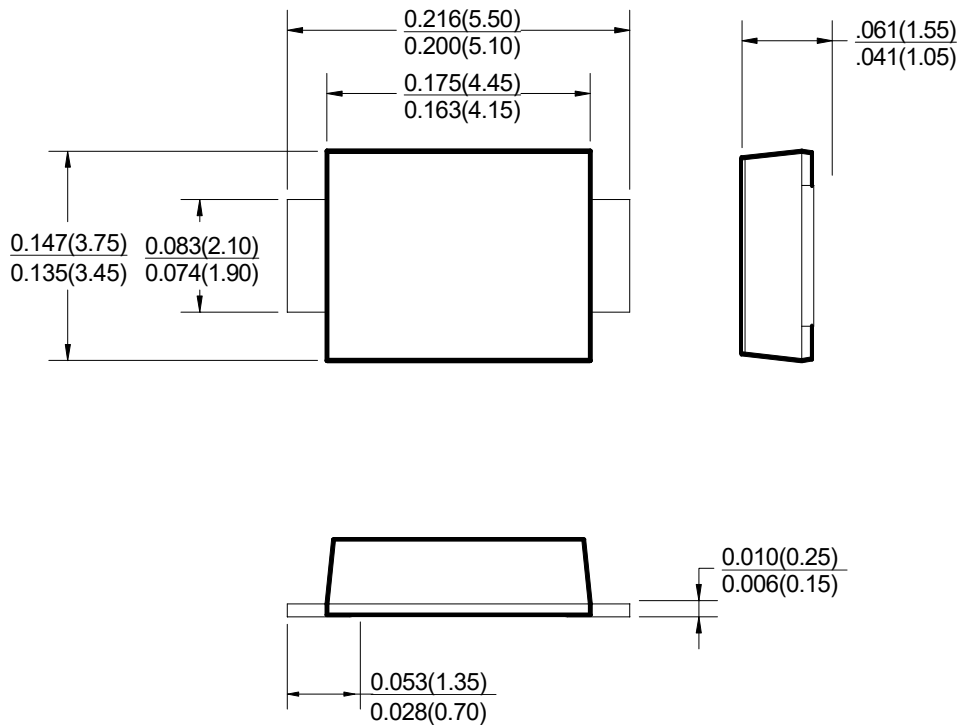


FIG.5: Diagram of circuit and Testing wave form of reverse recovery time

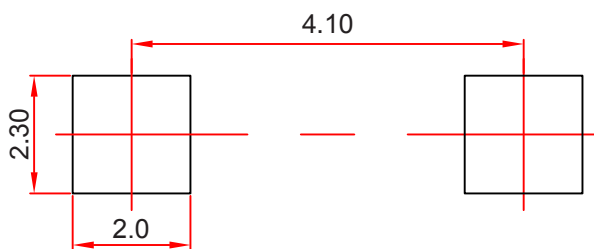


SMBF Package Outline Dimensions



Dimensions in inches and (millimeters)

SMBF Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.

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